

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCX16501FT

Low-Voltage 18-Bit Universal Bus Transceiver with 3.6-V Tolerant Inputs and Outputs

The TC74VCX16501FT is a high performance CMOS 18-bit universal bus transceiver. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to 3.6 V.

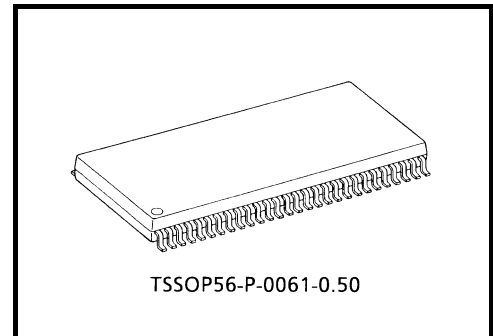
Data flow in each direction is controlled by output-enable (OEAB and OEBA), latch-enable (LEAB and LEBA), and clock (CKAB and CKBA) inputs.

For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CKAB is held at a high or low logic level. If LEAB is low, the A bus data is stored in the latch/flip-flop on the low-to-high transition of CKAB.

Data flow for B to A is similar to that of A to B but uses $\overline{\text{OEBA}}$, LEBA, and CKBA.

When the OE input is high, the outputs are in a high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge.



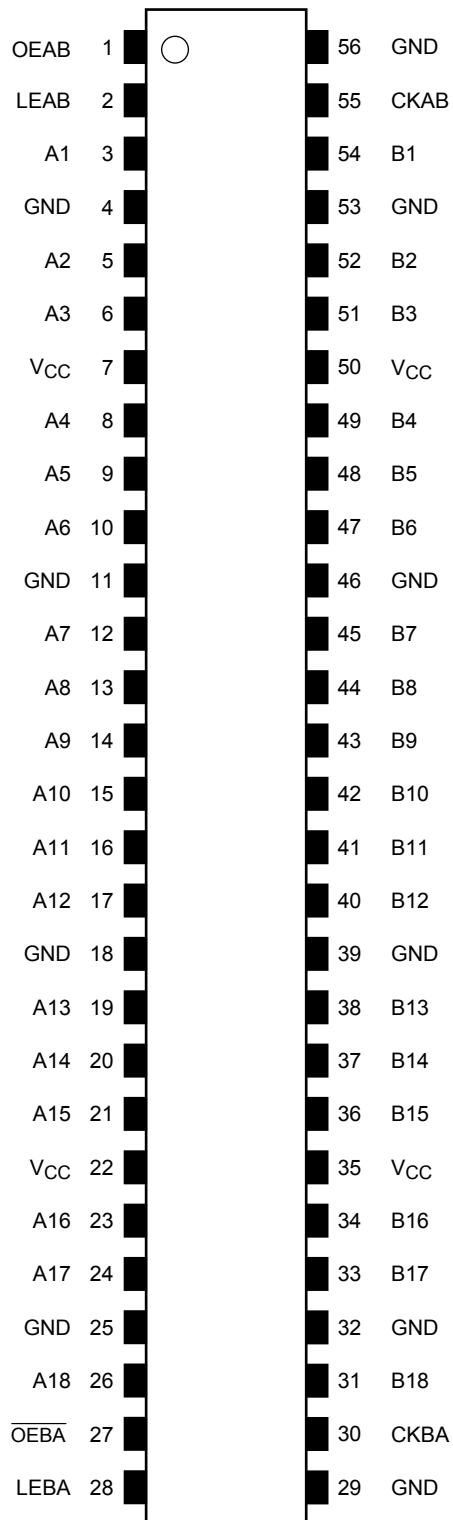
Weight: 0.25 g (typ.)

Features (Note)

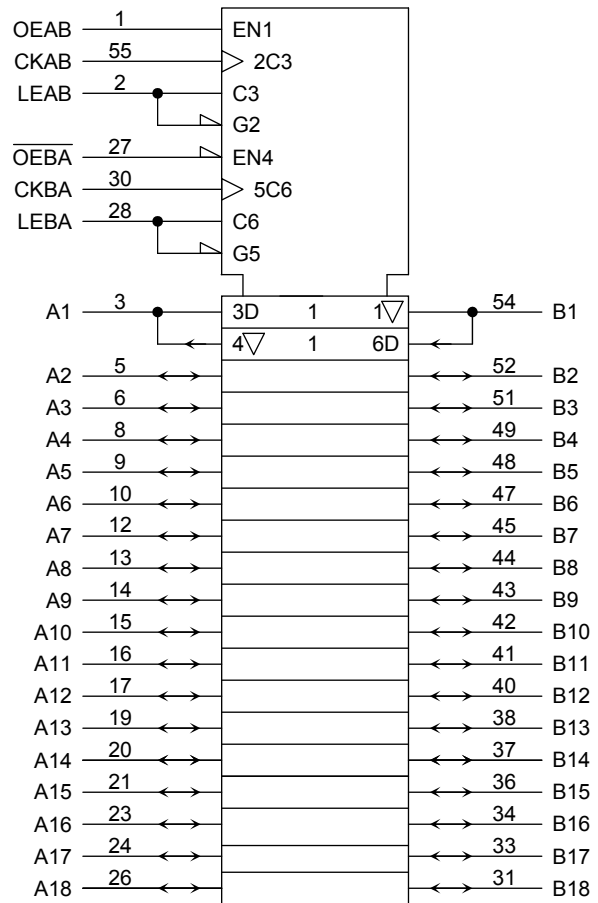
- Low-voltage operation: $V_{CC} = 1.8$ to 3.6 V
- High-speed operation: $t_{pd} = 2.9$ ns (max) ($V_{CC} = 3.0$ to 3.6 V)
 : $t_{pd} = 3.5$ ns (max) ($V_{CC} = 2.3$ to 2.7 V)
 : $t_{pd} = 7.0$ ns (max) ($V_{CC} = 1.8$ V)
- Output current: $I_{OH}/I_{OL} = \pm 24$ mA (min) ($V_{CC} = 3.0$ V)
 : $I_{OH}/I_{OL} = \pm 18$ mA (min) ($V_{CC} = 2.3$ V)
 : $I_{OH}/I_{OL} = \pm 6$ mA (min) ($V_{CC} = 1.8$ V)
- Latch-up performance: ± 300 mA
- ESD performance: Machine model $> \pm 200$ V
 : Human body model $> \pm 2000$ V
- Package: TSSOP (thin shrink small outline package)
- Bidirectional interface between 2.5 V and 3.3 V signals.
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

Note: Do not apply a signal to any bus pins when it is in the output mode. Damage may result.
 All floating (high impedance) bus pins must have their input level fixed by means of pull-up or pull-down resistors.



Pin Assignment (top view)



IEC Logic Symbol





Truth Table (A bus → B bus)

Inputs				Outputs B
OEAB	LEAB	CKAB	A	
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L		L	L
H	L		H	H
H	L	H	X	B0 (Note)
H	L	L	X	B0 (Note)

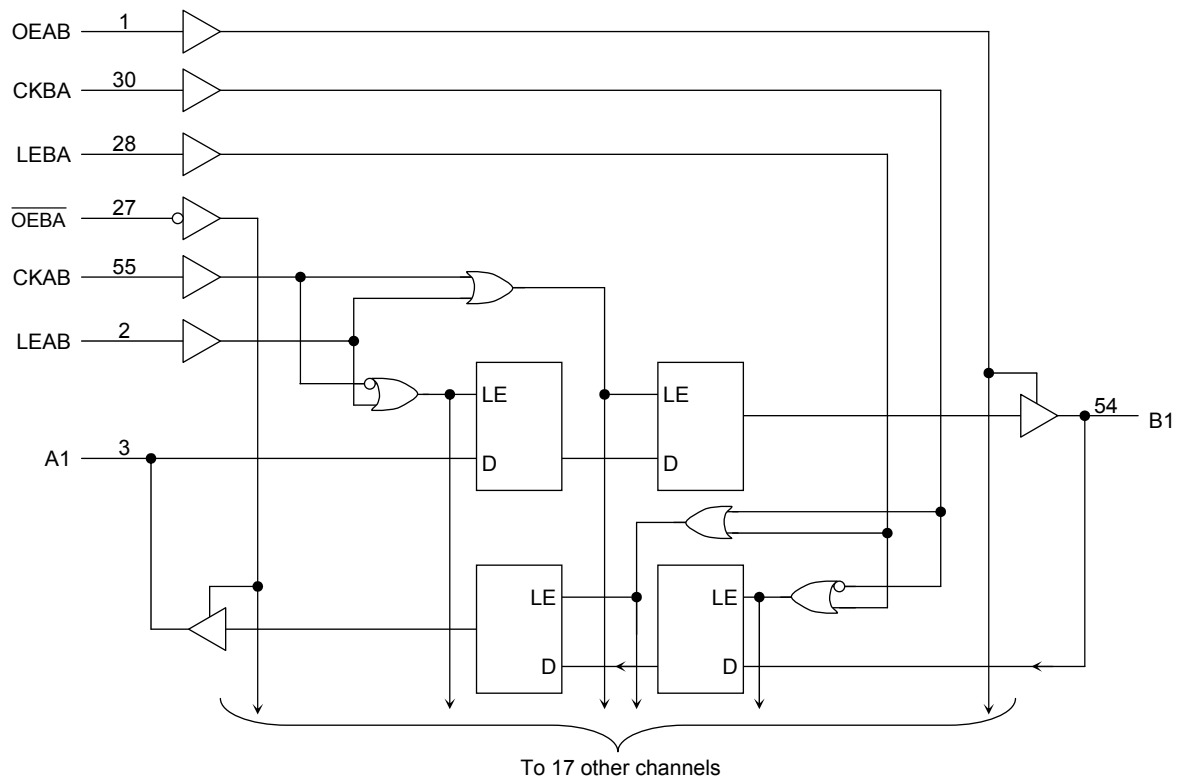
Note: Output level before the indicated steady-state input conditions were established, provided that CKAB was low or high before LEAB went low.

Truth Table (B bus → A bus)

Inputs				Outputs A
$\overline{\text{OEBA}}$	LEBA	CKBA	B	
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L		L	L
L	L		H	H
L	L	H	X	A0 (Note)
L	L	L	X	A0 (Note)

Note: Output level before the indicated steady-state input conditions were established, provided that CKBA was low or high before LEBA went low.

System Diagram



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	-0.5 to 4.6	V
DC input voltage (OEAB, \overline{OEBA} , LEAB, LEBA, CKAB, CKBA)	V_{IN}	-0.5 to 4.6	V
DC bus I/O voltage	$V_{I/O}$	-0.5 to 4.6 (Note 2)	V
		-0.5 to $V_{CC} + 0.5$ (Note 3)	
Input diode current	I_{IK}	-50	mA
Output diode current	I_{OK}	± 50 (Note 4)	mA
DC output current	I_{OUT}	± 50	mA
Power dissipation	P_D	400	mW
DC V_{CC} /ground current per supply pin	I_{CC}/I_{GND}	± 100	mA
Storage temperature	T_{stg}	-65 to 150	$^{\circ}C$

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Note 2: OFF state

Note 3: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Recommended Operating Range (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	1.8 to 3.6	V
		1.2 to 3.6 (Note 2)	
Input voltage (OEAB, OEBA, LEAB, LEBA, CKAB, CKBA)	V _{IN}	-0.3 to 3.6	V
Bus I/O voltage	V _{I/O}	0 to 3.6 (Note 3)	V
		0 to V _{CC} (Note 4)	
Output current	I _{OH} /I _{OL}	±24 (Note 5)	mA
		±18 (Note 6)	
		±6 (Note 7)	
Operating temperature	T _{opr}	-40 to 85	°C
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V

Note 1: The recommended operating conditions are required to ensure the normal operation of the device.
Unused inputs must be tied to either V_{CC} or GND.

Note 2: Data retention only

Note 3: OFF state

Note 4: High or low state

Note 5: V_{CC} = 3.0 to 3.6 V

Note 6: V_{CC} = 2.3 to 2.7 V

Note 7: V_{CC} = 1.8 V

Note 8: V_{IN} = 0.8 to 2.0 V, V_{CC} = 3.0 V

Electrical Characteristics

DC Characteristics (Ta = -40 to 85°C, 2.7 V < VCC ≤ 3.6 V)

Characteristics		Symbol	Test Condition		VCC (V)	Min	Max	Unit
Input voltage	H-level	V _{IH}	—		2.7 to 3.6	2.0	—	V
	L-level	V _{IL}	—		2.7 to 3.6	—	0.8	
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2	—	V
				I _{OH} = -12 mA	2.7	2.2	—	
				I _{OH} = -18 mA	3.0	2.4	—	
				I _{OH} = -24 mA	3.0	2.2	—	
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7 to 3.6	—	0.2	
				I _{OL} = 12 mA	2.7	—	0.4	
				I _{OL} = 18 mA	3.0	—	0.4	
				I _{OL} = 24 mA	3.0	—	0.55	
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	—	±5.0	μA
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.7 to 3.6	—	±10.0	μA
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		2.7 to 3.6	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7 to 3.6	—	±20.0	
Increase in I _{CC} per input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V		2.7 to 3.6	—	750	

DC Characteristics (Ta = -40 to 85°C, 2.3 V ≤ VCC ≤ 2.7 V)

Characteristics		Symbol	Test Condition		VCC (V)	Min	Max	Unit
Input voltage	H-level	V _{IH}	—		2.3 to 2.7	1.6	—	V
	L-level	V _{IL}	—		2.3 to 2.7	—	0.7	
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	—	V
				I _{OH} = -6 mA	2.3	2.0	—	
				I _{OH} = -12 mA	2.3	1.8	—	
				I _{OH} = -18 mA	2.3	1.7	—	
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3 to 2.7	—	0.2	
				I _{OL} = 12 mA	2.3	—	0.4	
				I _{OL} = 18 mA	2.3	—	0.6	
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		2.3 to 2.7	—	±5.0	μA
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.3 to 2.7	—	±10.0	μA
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		2.3 to 2.7	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3 to 2.7	—	±20.0	

DC Characteristics (Ta = -40 to 85°C, 1.8 V ≤ VCC < 2.3 V)

Characteristics		Symbol	Test Condition		VCC (V)	Min	Max	Unit
Input voltage	H-level	V _{IH}	—		1.8 to 2.3	0.7 × V _{CC}	—	V
	L-level	V _{IL}	—		1.8 to 2.3	—	0.2 × V _{CC}	
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	—	V
				I _{OH} = -6 mA	1.8	1.4	—	
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.8	—	0.2	
				I _{OL} = 6 mA	1.8	—	0.3	
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		1.8	—	±5.0	μA
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		1.8	—	±10.0	μA
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		1.8	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		1.8	—	±20.0	

AC Characteristics (Ta = -40 to 85°C, input: tr = tf = 2.0 ns, CL = 30 pF, RL = 500 Ω) (Note 1)

Characteristics	Symbol	Test Condition	VCC (V)	Min	Max	Unit
Maximum clock frequency	f _{max}	Figure 1, Figure 3	1.8	100	—	MHz
			2.5 ± 0.2	200	—	
			3.3 ± 0.3	250	—	
Propagation delay time (An, Bn-Bn, An)	t _{pLH} t _{pHL}	Figure 1, Figure 2	1.8	1.5	7.0	ns
			2.5 ± 0.2	0.8	3.5	
			3.3 ± 0.3	0.6	2.9	
Propagation delay time (CKAB, CLKBA-Bn, An)	t _{pLH} t _{pHL}	Figure 1, Figure 3	1.8	1.5	8.8	ns
			2.5 ± 0.2	0.8	4.4	
			3.3 ± 0.3	0.6	3.5	
Propagation delay time (LEAB, LEBA-Bn, An)	t _{pLH} t _{pHL}	Figure 1, Figure 4	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	4.9	
			3.3 ± 0.3	0.6	3.8	
Output enable time (OEAB, OEBA-Bn, An)	t _{pZL} t _{pZH}	Figure 1, Figure 5, Figure 6	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	4.9	
			3.3 ± 0.3	0.6	3.8	
Output disable time (OEAB, OEBA-Bn, An)	t _{pLZ} t _{pHZ}	Figure 1, Figure 5, Figure 6	1.8	1.5	7.6	ns
			2.5 ± 0.2	0.8	4.2	
			3.3 ± 0.3	0.6	3.7	
Minimum pulse width	t _W (H) t _W (L)	Figure 1, Figure 3, Figure 4	1.8	4.0	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum set-up time	t _s	Figure 1, Figure 3, Figure 4	1.8	2.5	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum hold time	t _h	Figure 1, Figure 3, Figure 4	1.8	1.0	—	ns
			2.5 ± 0.2	1.0	—	
			3.3 ± 0.3	1.0	—	
Output to output skew	t _{osLH} t _{osHL}	(Note 2)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

Note 1: For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic Switching Characteristics

($T_a = 25^\circ\text{C}$, input: $t_r = t_f = 2.0 \text{ ns}$, $C_L = 30 \text{ pF}$, $R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V _{OL}	V _{OLP}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note)	1.8	0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note)	2.5	0.6	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note)	3.3	0.8	
Quiet output minimum dynamic V _{OL}	V _{OLV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note)	1.8	-0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note)	2.5	-0.6	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note)	3.3	-0.8	
Quiet output minimum dynamic V _{OH}	V _{OHV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note)	1.8	1.5	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note)	2.5	1.9	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note)	3.3	2.2	

Note: Parameter guaranteed by design.

Capacitive Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Input capacitance	C _{IN}	—	1.8, 2.5, 3.3	6	pF
Bus I/O capacitance	C _{I/O}	—	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (Note)	1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC(\text{opr})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/18 \text{ (per bit)}$$

AC Test Circuit

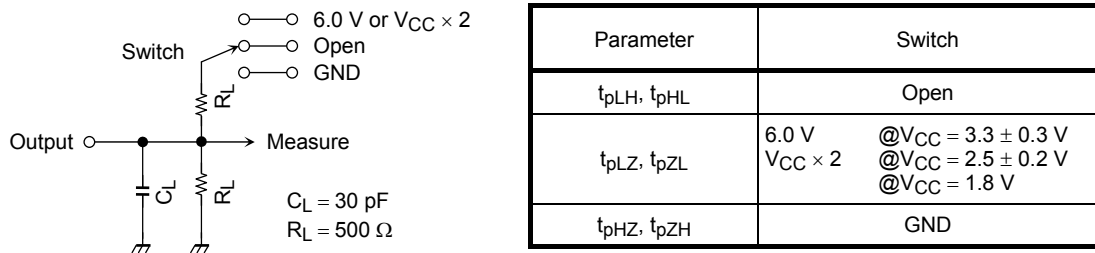


Figure 1

AC Waveform

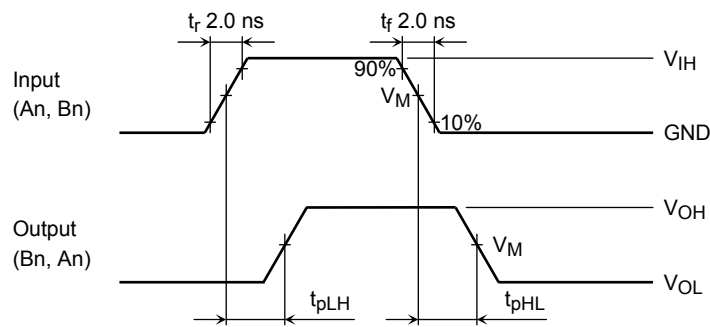


Figure 2 t_{pLH}, t_{pHL}

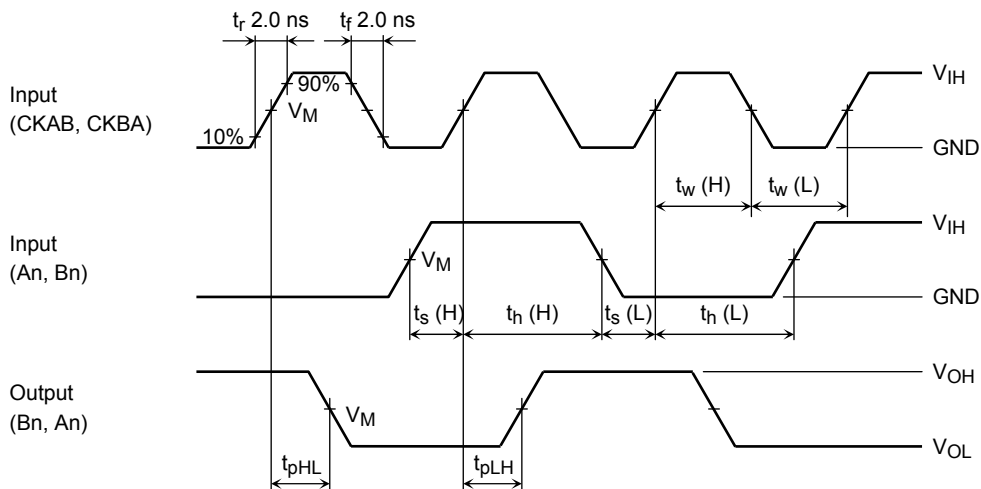


Figure 3 $t_{pLH}, t_{pHL}, t_w, t_s, t_h$

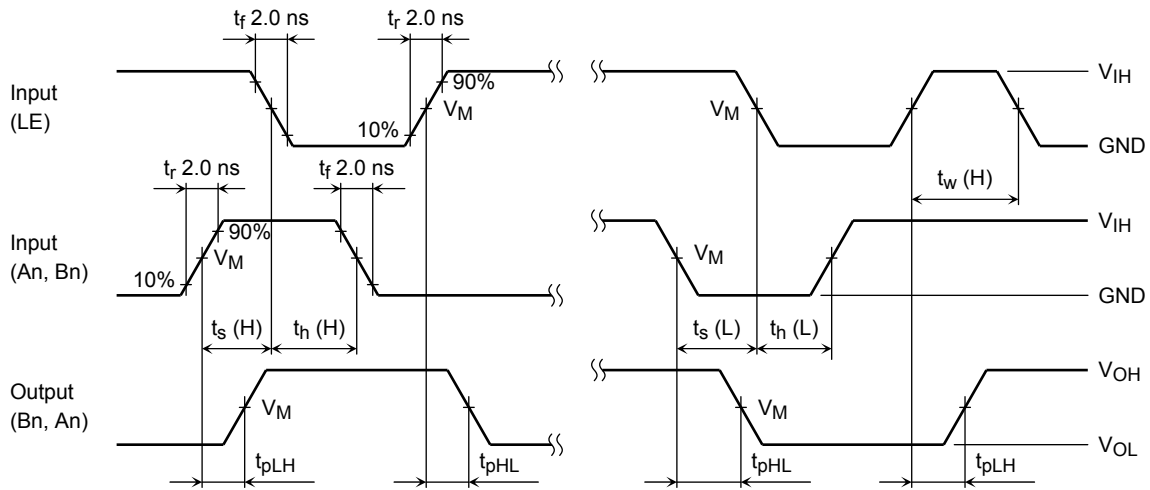


Figure 4 t_{pLH} , t_{pHL} , t_w , t_s , t_h

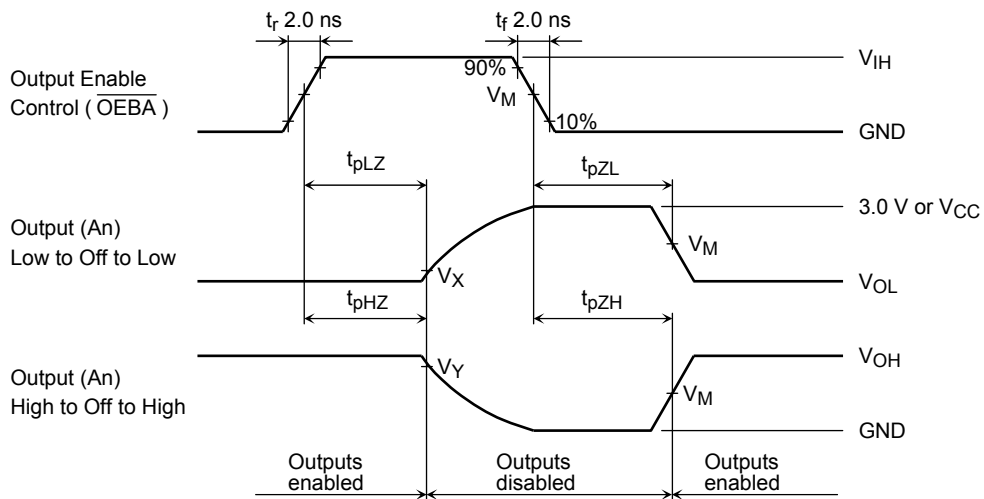


Figure 5 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

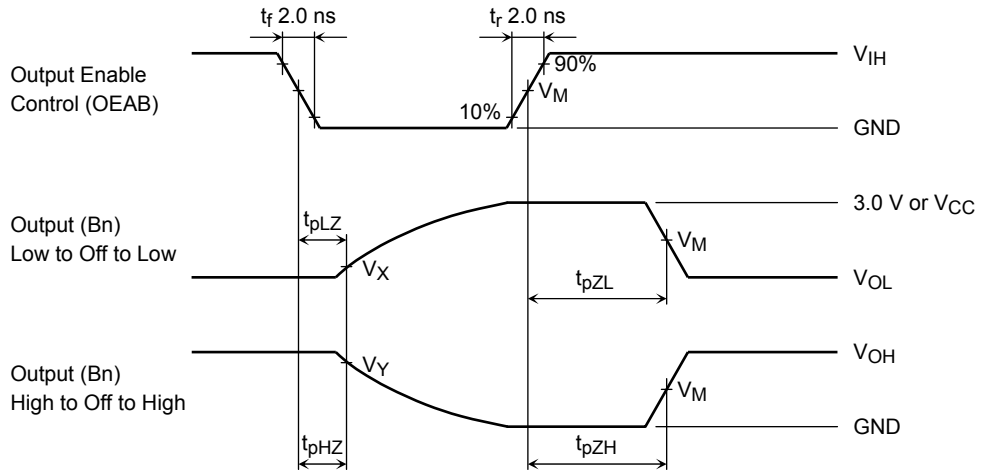


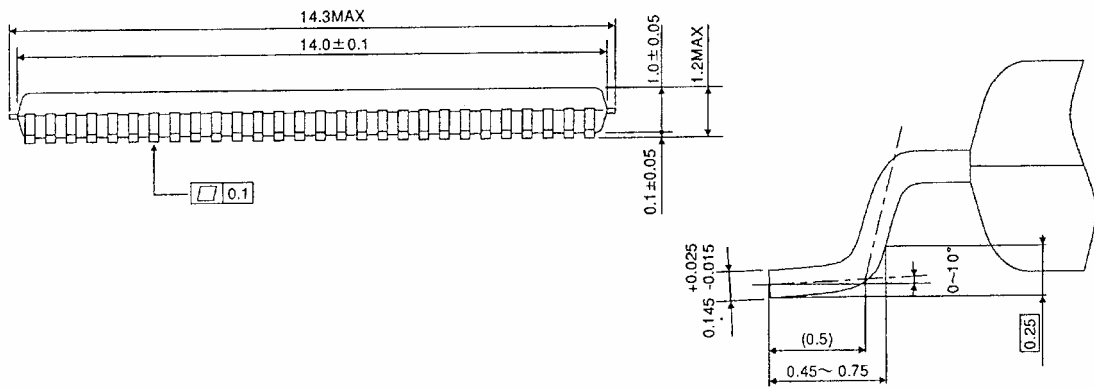
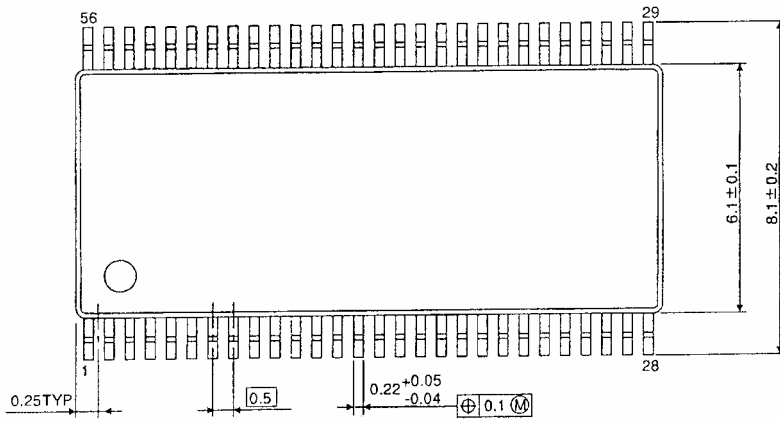
Figure 6 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol	V_{CC}		
	$3.3 \pm 0.3 \text{ V}$	$2.5 \pm 0.2 \text{ V}$	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$
V_X	$V_{OL} + 0.3 \text{ V}$	$V_{OL} + 0.15 \text{ V}$	$V_{OL} + 0.15 \text{ V}$
V_Y	$V_{OH} - 0.3 \text{ V}$	$V_{OH} - 0.15 \text{ V}$	$V_{OH} - 0.15 \text{ V}$

Package Dimensions

TSSOP56-P-0061-0.50

Unit : mm



Weight: 0.25 g (typ.)

Note: Lead (Pb)-Free Packages**TSSOP56-P-0061-0.50****RESTRICTIONS ON PRODUCT USE**

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